

IR-1649 (2-1939)

TRENCH FET WITH NON OVERLAPPING POLY
AND REMOTE CONTACT THEREFOR

5

ABSTRACT OF THE DISCLOSURE

10 A power MOSFET has a plurality of spaced rows
of parallel coextensive trenches. The trenches are lined
with a gate oxide and are filled with conductive
polysilicon. Spaced narrow polysilicon strips overlies
the silicon surface and connects adjacent trenches to one
another. The source contact is made at a location remote
from the trenches and between the rows of trenches. The
trenches are 1.8 microns deep, are 0.6 microns wide and
15 are spaced by about 0.6 microns or greater. The device
has a very low figure of merit and is useful especially
in low voltage circuits.